

**Listing of Claims:**

1. (Currently Amended) A semiconductor device comprising:  
a semiconductor substrate having a plurality of connecting  
pads on one surface;

an insulating film which is formed of a single layer and  
5 covers said one surface of the semiconductor substrate, and which  
includes: (i) a plurality of holes extending through the  
insulating film, each of the holes corresponding to one of the  
connecting pads, and (ii) at least one recess extending partially  
10 through the insulating film such that a bottom surface of the  
recess is depressed with respect to an upper surface of the  
insulating film in a direction of thickness of the insulating  
film, each said recess including a first portion through which  
one of the holes extends and which surrounds a periphery of the  
one of the holes and a second portion which extends outwardly  
15 from the first portion; and

at least one interconnection including at least one  
conductive layer having: (i) a first section formed on the bottom  
surface of a corresponding said at least one recess to extend  
along the bottom surface, over the first portion and the second  
20 portion of the recess, ~~each said at least one interconnection and~~  
(ii) a second section that is being directly contacted to a  
corresponding one of the connecting pads through a corresponding

one of the holes in the insulating film, ~~and each~~ said at least one ~~interconnection~~ conductive layer being formed of a same material along an entire length thereof, including the first section and the second section.

Claim 2 (Canceled).

3. (Currently Amended) A device according to claim 1, wherein each said recess in the insulating film has a pair of side surfaces, and a space is provided between each said at least one interconnection and a corresponding side surface ~~the side surfaces~~ of the recess in which the interconnection is provided.

4. (Previously Presented) A device according to claim 1, wherein the at least one interconnection comprises a connecting pad portion, and

wherein the semiconductor device further comprises:

a bump electrode formed on the connecting pad portion, and

an encapsulating film formed around the bump electrode and on the insulating film and the at least one interconnection.

5. (Withdrawn) A device according to claim 4, further comprising an upper insulating film formed between the insulating

film and the encapsulating film, said upper insulating film having a hole formed in a portion corresponding to each said bump electrode.

6. (Withdrawn) A device according to claim 5, wherein the insulating film and upper insulating film are made of materials containing a same main component.

7. (Withdrawn) A device according to claim 5, wherein the upper insulating film and the encapsulating film are made of different materials.

8. (Withdrawn) A device according to claim 4, wherein each said bump electrode protrudes from an upper surface of the encapsulating film.

9. (Withdrawn) A device according to claim 4, wherein each said bump electrode comprises a lower bump electrode and an upper bump electrode formed on the lower bump electrode.

10. (Withdrawn) A device according to claim 9, wherein the lower bump electrode protrudes from an upper surface of the encapsulating film.

11. (Withdrawn) A device according to claim 1, wherein the at least one interconnection comprises a connecting pad portion formed on the corresponding one of the connecting pads to which the interconnection is connected, and

5 wherein the semiconductor device further comprises:

at least one bump electrode formed on the connecting pad portion of the at least one interconnection, and

an encapsulating film formed around the bump electrode and on the insulating film.

12. (Original) A device according to claim 1, wherein the insulating film is made of an organic resin.

13. (Previously Presented) A device according to claim 1, wherein the recess in the insulating film has a depth which is not less than a thickness of the interconnection.

14. (Original) A device according to claim 1, wherein the insulating film has a thickness of 10 to 30  $\mu\text{m}$ .

15. (Original) A device according to claim 1, wherein the recess has a depth of 5 to 15  $\mu\text{m}$ .

16. (Previously Presented) A device according to claim 15, wherein a distance between a bottom surface of the insulating film and the bottom surface of the recess is not less than 1  $\mu\text{m}$ .

Claims 17-35 (Canceled).

36. (Currently Amended) A semiconductor device comprising:  
a semiconductor substrate having a plurality of connecting pads on one surface;

an insulating film which covers said one surface of the semiconductor substrate, and which includes: (i) a plurality of holes extending through the insulating film, each of the holes corresponding to one of the connecting pads, and (ii) at least one recess extending partially through the insulating film such that a bottom surface of the recess is depressed with respect to an upper surface of the insulating film in a direction of thickness of the insulating film, each said recess extending from a first position at an edge of one of said holes to a second position outside an area above the connecting pad to which said one of the holes corresponds; and

at least one interconnection formed on the bottom surface of a corresponding said at least one recess to extend along the bottom surface, each said at least one interconnection being

connected to a corresponding one of the connecting pads through a corresponding one of the holes in the insulating film;

20        wherein each said at least one recess in the insulating film has a pair of side surfaces, and a space is provided between each said at least one interconnection and the side surfaces of the recess in which the interconnection is provided.

37. (Currently Amended) A semiconductor device comprising:  
a semiconductor substrate having a plurality of connecting pads on one surface;

5        a protective film formed of a single layer, said protective film including: (i) a plurality of holes extending completely through the protective film, each of the holes corresponding to one of the connecting pads, and (ii) a plurality of recesses extending partially through the protective film, each of said recesses having a recessed surface that is lower than an upper  
10        surface of the protective film in a thickness direction of the protective film, and each of said recesses extending from a first position at an edge of one of said holes to a second position outside an area above the connecting pad to which said one of the holes corresponds; and

15        interconnections which are respectively connected to the connecting pads through the holes in the protective film, and

which are provided on the recessed surfaces of the protective film to extend along the recessed surfaces;

20 wherein each of the recesses in the protective film has a pair of side surfaces, and a space is provided between each of the interconnections and a corresponding side surface ~~the side surfaces~~ of the recess in which the interconnection is provided.

38. (Previously Presented) A device according to claim 36, wherein the insulating film is formed of a single layer.

39. (Previously Presented) A device according to claim 36, wherein the at least one interconnection comprises a connecting pad portion, and

wherein the semiconductor device further comprises:

5 a bump electrode formed on the connecting pad portion, and

an encapsulating film formed around the bump electrode and on the insulating film and the at least one interconnection.

Claims 40-45 (Canceled).

46. (Previously Presented) A device according to claim 36, wherein the at least one interconnection comprises a connecting

pad portion formed on the corresponding one of the connecting pads to which the interconnection is connected, and

5            wherein the semiconductor device further comprises:

             at least one bump electrode formed on the connecting pad portion of the at least one interconnection, and

             an encapsulating film formed around the bump electrode and on the insulating film.

47. (Previously Presented) A device according to claim 36, wherein the insulating film is made of an organic resin.

48. (Currently Amended) A device according to claim ~~±~~ 36, wherein the recess in the insulating film has a depth which is not less than a thickness of the interconnection.

49. (Previously Presented) A device according to claim 36, wherein the insulating film has a thickness of 10 to 30  $\mu\text{m}$ .

50. (Previously Presented) A device according to claim 36, wherein the recess has a depth of 5 to 15  $\mu\text{m}$ .

51. (Currently Amended) A device according to claim ~~±~~ 50, wherein a distance between a bottom surface of the insulating film and the bottom surface of the recess is not less than 1  $\mu\text{m}$ .



52. (Currently Amended) A semiconductor device comprising:  
a semiconductor substrate having a plurality of connecting  
pads on one surface;

a protective film formed of a single layer, said protective  
5 film including: (i) a plurality of holes extending completely  
through the protective film, each of the holes corresponding to  
one of the connecting pads, and (ii) a plurality of recesses  
extending partially through the protective film, each of said  
recesses having a recessed surface that is lower than an upper  
10 surface of the protective film in a thickness direction of the  
protective film, and each of said recesses including a first  
portion through which one of the holes extends and which  
surrounds a periphery of the one of the holes and a second  
portion which extends outwardly from the first portion; and

15 a plurality of interconnections, each of which are  
respectively includes at least one conductive layer having: (i) a  
second section directly connected to a corresponding one of the  
connecting pads through a corresponding one of the holes in the  
protective film, and ~~which are~~ (ii) a first section provided on a  
20 corresponding one of the recessed surfaces of the protective film  
to extend along the corresponding one of the recessed surfaces  
over the first and second portions ~~thereof, of the recessed~~  
~~surfaces, and each of which is~~ said at least one conductive layer

being formed of a same material along an entire length thereof,  
25 including the first section and the second section.

53. (Currently Amended) A device according to claim 1,  
wherein the at least one interconnection comprises a lower  
conductive layer and an upper conductive layer formed on an  
entire upper surface of the lower conductive layer so as not to  
laterally ~~extend from~~ project past the upper surface of the lower  
conductive layer.